

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0033] of page 16 with the following amended paragraph:

An alternative method of forming the body region 205 from the silicon layer 265 is illustrated in FIGUREs 2D-2E. This method is particularly advantageous when one wishes to form closely spaced, narrow body regions 205, for example, widths 245 (FIGURE 2E) of about 50 nanometers or less, and spaced apart by 50 nanometers. In other words, the pitch, the sum of the width of the body and the space between body regions, can be 100 nanometers or less. The use of sidewall masks 277 shown in FIGUREs 2D and 2E advantageously allows a doubling of minimum pitch normally allowed by conventional lithographic techniques because there is a sidewall on each side of the initially patterned structure. Of course, one skilled in the art would understand that there are other ways, such as patterning followed by over-etch, to facilitate the formation of sublithographic widths.